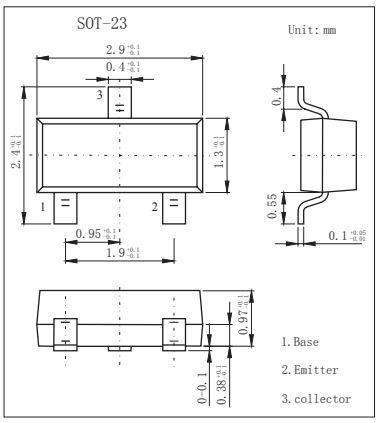
PNP Transistors
KST9012



■ Features

- Excellent h_{FE} liearity
- Collector Current :I_C=-0.5A

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-25	V
Emitter - Base Voltage	V_{EBO}	-5	V
Collector Current to Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector - base breakdown voltage	V_{CBO}	I_C= -100u A, I_E=0	-40			V
Collector - emitter breakdown voltage	V_{CEO}	I_C= -1 mA , I_B=0	-25			V
Emitter - base breakdown voltage	V_{EBO}	I_E= -100uA, I_C=0	-5			V
Collector cut - off current	I_{CBO}	V_{CB}=- 40V, I_E=0			-0.1	μA
Collector cut - off current	I_{CEO}	V_{CB}=-20V, I_E=0			-0.1	μA
Emitter cut - off current	I_{EBO}	V_{EB}=- 5V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C= -50mA	120		400	
Collector - emitter saturation voltage	$V_{CE(sat)}$	I_C= -500 mA, I_B= -50mA			-0.6	V
Base - emitter voltage	$V_{BE(sat)}$	I_C= -500 mA, I_B=- 50mA			-1.2	V
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			5	pF
Transition frequency	f_T	V_{CE}=-6V, I_C=-20mA,f=30MHz	150			MHz

■ Classification of $h_{fe(1)}$

Marking	2T1			
Rank		L	H	J
Range	200-350	120-200	144-202	300-400

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■ Typical Characteristics